

- ★ Super_Junction technology
- ★ Much lower $R_{on} \cdot A$ performance for On-state efficiency
- ★ Better efficiency due to very low FOM
- ★ Qualified for industrial grade applications according to JEDEC

650V Super Junction Power MOSFET

Product Summary



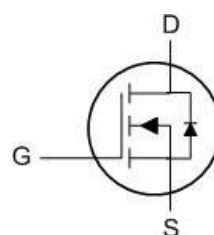
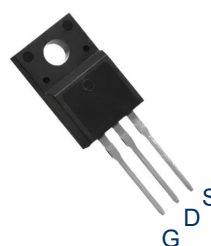
BVDSS	RDSON	ID
650V	0.43Ω	8A

Description

The XR65R500FT use super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

The XR65R500FT meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

TO220F Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	650	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	8	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	5	A
I_{DM}	Pulsed Drain Current ²	32	A
EAS	Single Pulse Avalanche Energy ³	65	mJ
I_{AS}	Avalanche Current	---	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation ⁴	73	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	143	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	1.7	$^\circ\text{C/W}$

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	650	---	---	V
$\Delta BV_{DSS} / \Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1mA$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=5.5A$	---	0.43	0.55	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	3	---	4	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=650V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=650V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=20V$, $I_D=4A$	---	6.6	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1MHz$	---	14	---	Ω
Q_g	Total Gate Charge	$V_{DS}=480V$, $V_{GS}=10V$, $I_D=5.5A$	---	15.6	---	nC
Q_{gs}	Gate-Source Charge		---	3.1	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DD}=400V$, $R_G=27\Omega$, $I_D=4A$	---	15	---	ns
T_r	Rise Time		---	17	---	
$T_{d(off)}$	Turn-Off Delay Time		---	78	---	
T_f	Fall Time		---	16	---	
C_{iss}	Input Capacitance	$V_{DS}=100V$, $V_{GS}=0V$, $f=1MHz$	---	470	---	pF
C_{oss}	Output Capacitance		---	25	---	
C_{rss}	Reverse Transfer Capacitance		---	0.47	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	8	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=5.5A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=5.5A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	210	---	nS
Q_{rr}	Reverse Recovery Charge		---	1.76	---	nC

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$ 3.The EAS data shows Max. rating . The test condition is $T_J = 25^\circ\text{C}$, $V_{DD}=200V$, $V_{GS}=10V$, $L=60mH$ 4.The power dissipation is limited by 150°C junction temperature5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Performance Characteristics

Fig 1. Output Characteristics ($T_j=25^\circ\text{C}$)

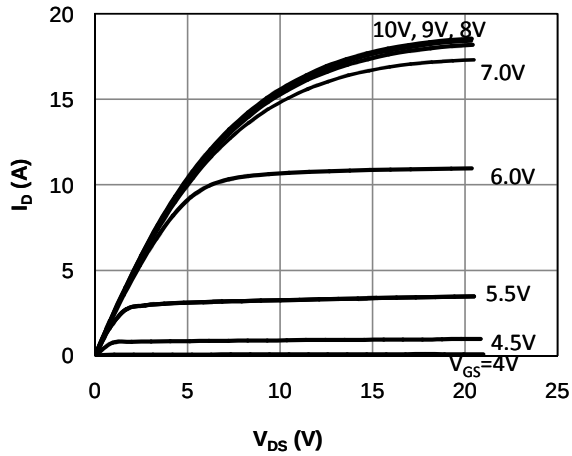


Fig 2. Output Characteristics ($T_j=150^\circ\text{C}$)

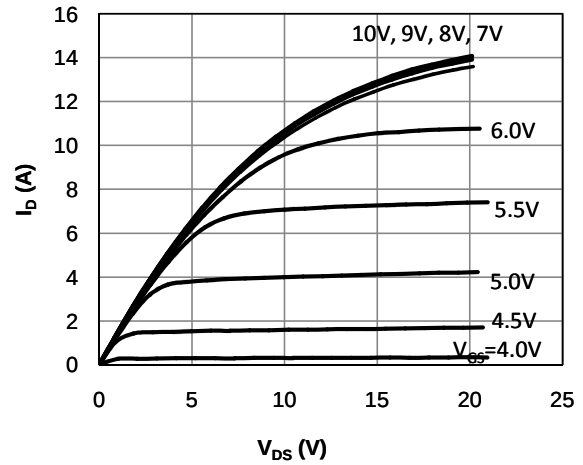


Fig 3: Transfer Characteristics

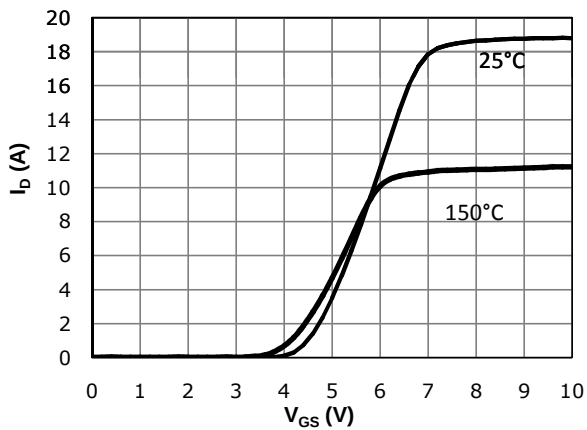


Fig 4: V_{TH} Vs T_j Temperature Characteristics

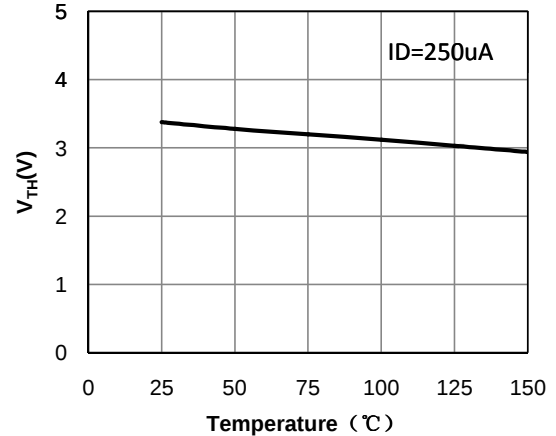


Fig 5: $R_{DS(on)}$ Vs I_{DS} Characteristics ($T_c=25^\circ\text{C}$)

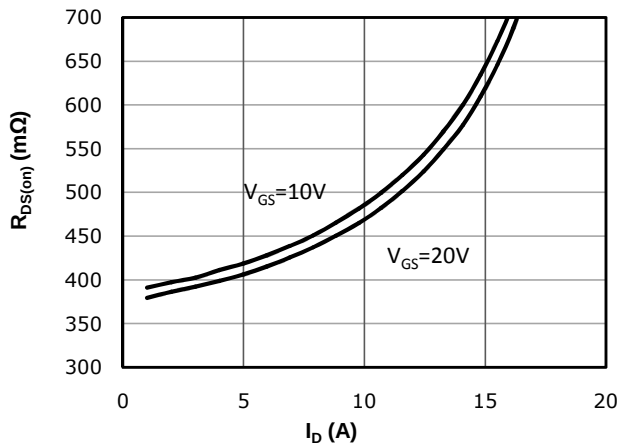
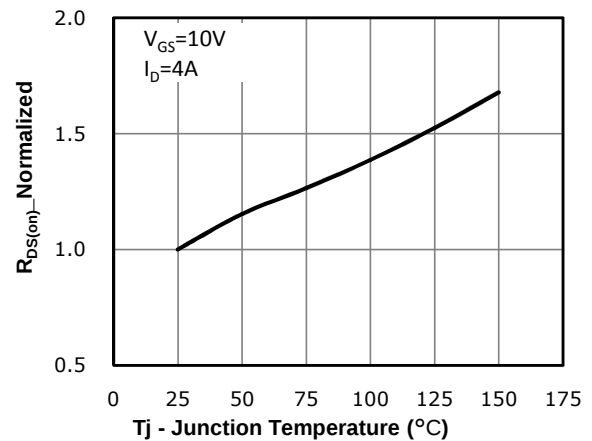


Fig 6: $R_{DS(on)}$ vs. Temperature



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Fig 7: BVDSS vs. Temperature

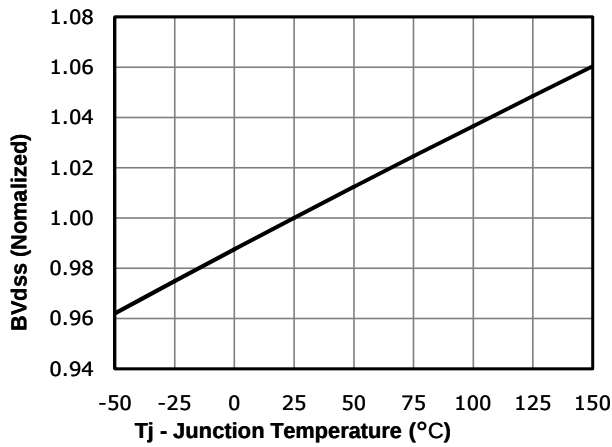


Fig 8: Rds(on) vs Gate Voltage

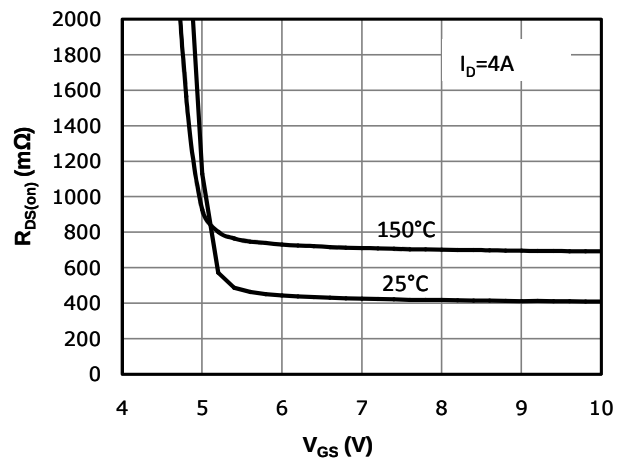


Fig 9: Body-diode Forward Characteristics

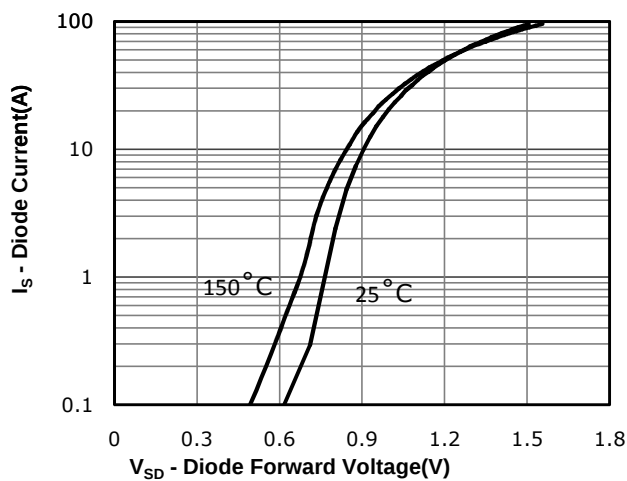


Fig 10: Gate Charge Characteristics

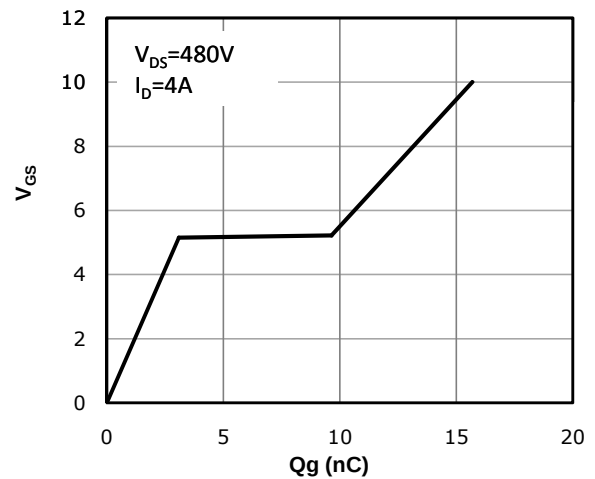


Fig 11: Capacitance Characteristics

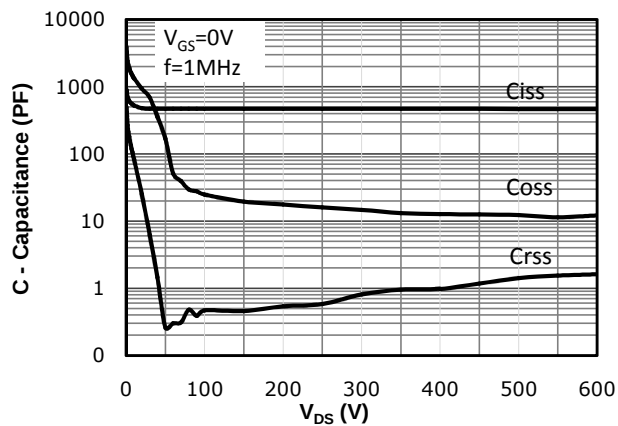
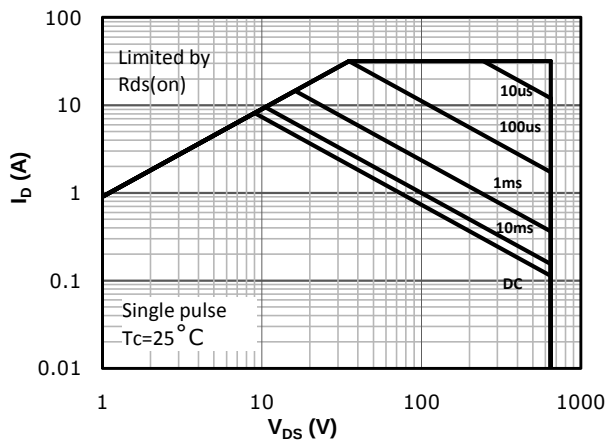
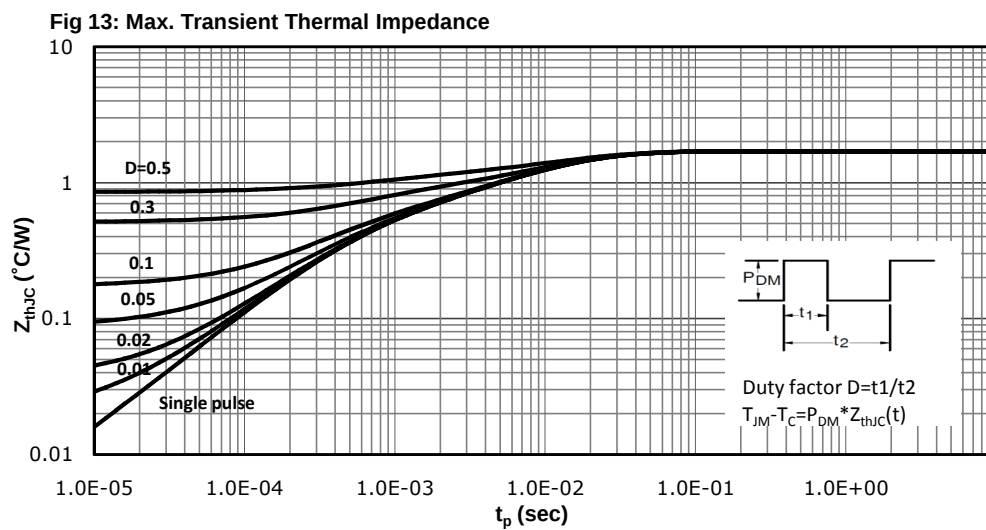


Fig 12: Safe Operating Area

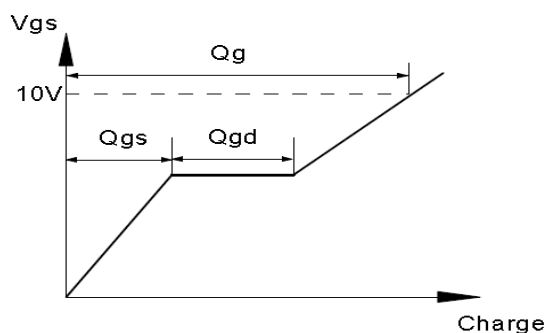
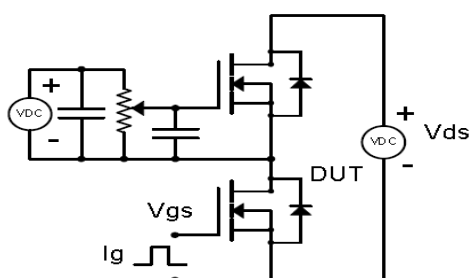


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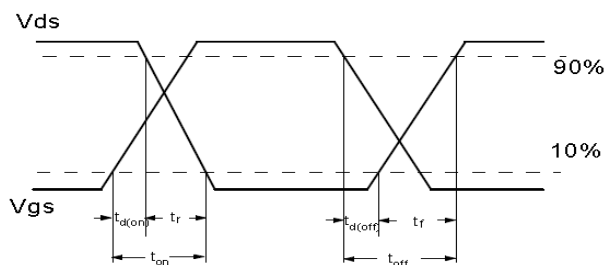
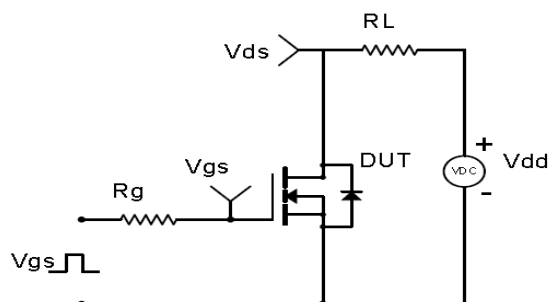


Test Circuit & Waveform

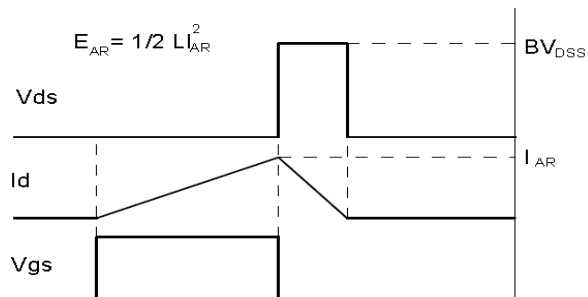
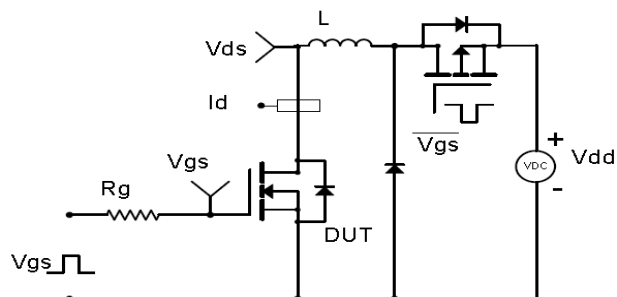
Gate Charge Test Circuit & Waveform



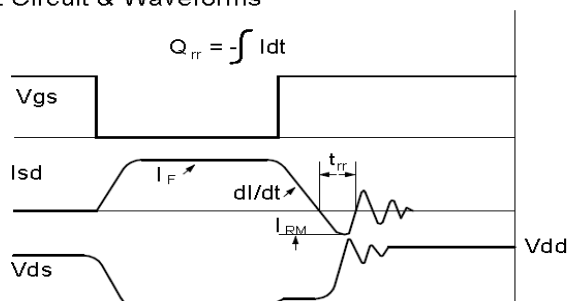
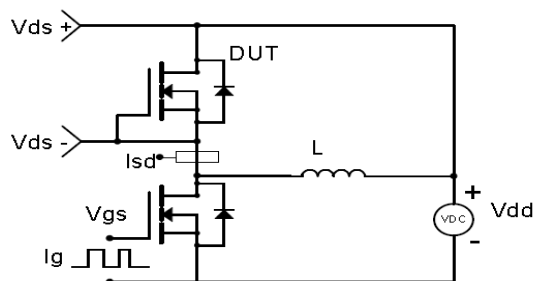
Resistive Switching Test Circuit & Waveforms



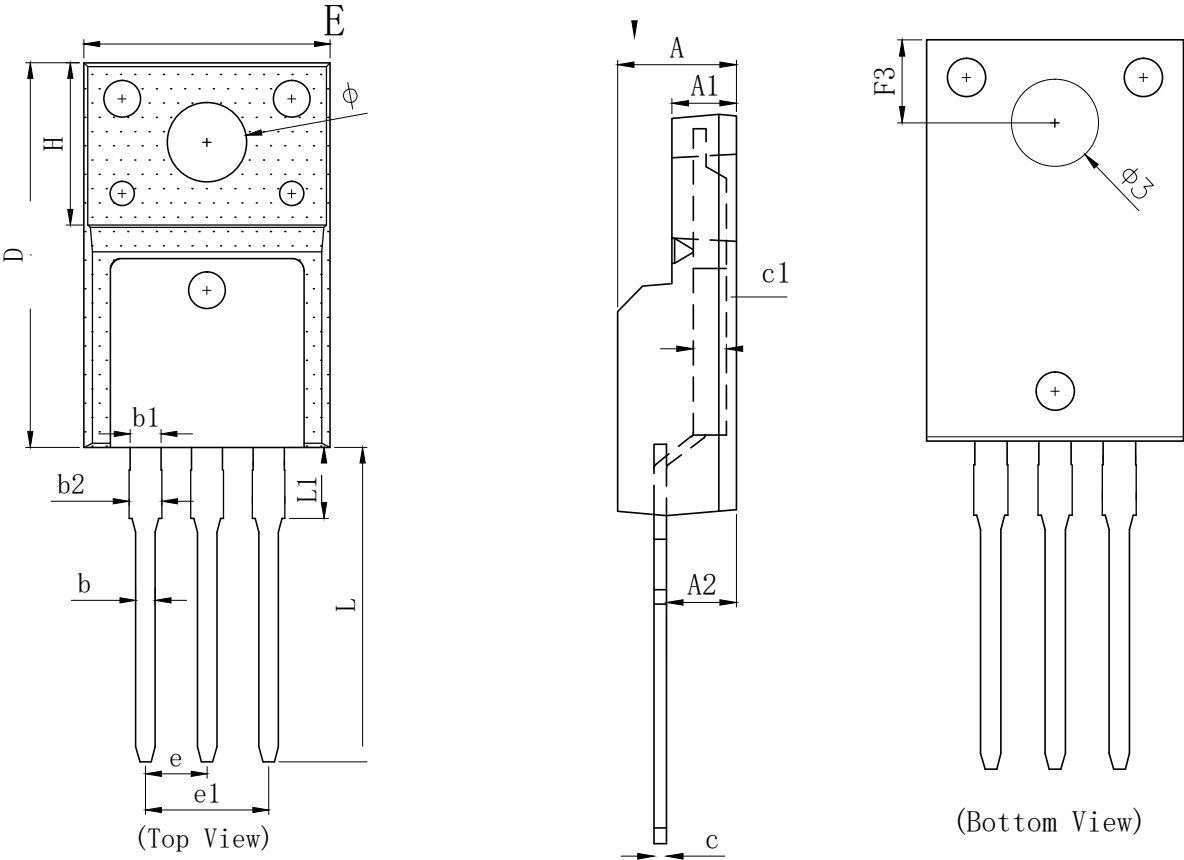
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Mechanical Dimensions for TO-220F



SYMBOL	MILLIMETER		
	MIN	Typ.	MAX
A	4.500	4.700	4.900
A1	2.340	2.540	2.740
A2	2.560	2.760	2.960
b	0.700	0.800	0.950
b1	1.180	1.280	1.430
b2	1.250	1.350	1.550
c	0.400	0.500	0.650
c1	1.200	1.300	1.350
D	15.570	15.870	16.170
H	6.700 REF		
E	9.960	10.160	10.360
e	2.540 BSC		
e1	5.080 BSC		
L	12.680	12.980	13.280
L1	2.780	2.930	3.080
F3	3.150	3.300	3.450
ϕ	3.030	3.180	3.450
$\phi 3$	3.150	3.450	3.650